Document Number: IMEH0017-8 Production Datasheet V1.0

DC-1.7GHz, 8W, 28V LDMOS Fully matched PA Module

Description

The IMEH0017-8 is a 8-watt ,single stage integrated Power Amplifier Module, designed for broad band applications, with frequencies from DC to 1.7GHz. The module is 50 Ω input/output matched and requires minimal external components.



The module implements distributed power amplifier in form of multi chips, housed in cost effective plastic open cavity package, offers a much lower cost than traditional MMIC solutions.

Vds=28V, Idq=150mA, CW

Parameter	30MHz	0.2GHz	0.5GHz	0.8GHz	1.0GHz	1.2GHz	1.5GHz	1.7GHz	Units
Linear Gain	22.5	21.7	20.9	20.0	19.9	18.8	20.3	20.3	dB
Pout@Pin=22dBm	9.8	9.8	10.2	9. 2	9.0	9.6	10.1	8.6	W
Gain@Pin=22dBm	18. 7	17.9	18. 1	17.7	17.5	17.8	18.0	17.4	dB
Eff@ Pin=22dBm	77	70	57	45	39	40	47	47	%

Product Features

• Operating Frequency Range: DC-1.7GHz

• Operating Drain Voltage: +28 V

• 50 Ω Input/Output

• Psat: ≥8W

• Small signal gain:>18dB, Power gain:>16dB

• Minimum efficiency:>35%

• 6x10 mm Surface Mount Package

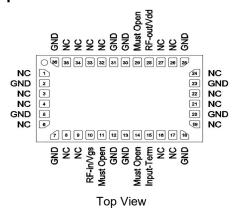
• Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

• Much lower cost than GaN-based ultrawide band PA, due to LDMOS technology used

Applications

- Ultra Broadband Amplifiers
- Fiber Drivers
- Test Instrumentation
- EMC Amplifier Drivers
- 2-way Radios

Pin Configuration and Description





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Pin No.	Symbol	Description
28	RFout/Vdd	Transistor 1, Drain Bias & RF Output
10	RFin/Vgs	Transistor 1, RF Input &Gate Bias
15	Input-Term	Transistor 1, Input 50 ohm term
Others	NC	No connection
11, 14, 29	Must Open	Keep the pin open, no GND
2,5,7,12,13,16,20,23,25, 30, 31,36 Package Base	GND	DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
DrainSource Voltage	V _{DSS}	65	Vdc
GateSource Voltage	V _{GS}	-10 to +10	Vdc
Operating Voltage	V_{DD}	+32	Vdc
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	Tc	+150	°C
Operating Junction Temperature	T,	+200	°C

Table 2. Thermal Characteristics

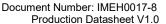
Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Do 10	2.2	°C/W
T _C = 87°C, T _J =175°C, DC test	R⊕JC	2.2	-0/00

Table 3. Electrical Characteristics

Parameter	Condition	Min	Тур	Max	Unit
Frequency Range		30		1700	MHz
Power Gain @ Psat		16			dB
P _{SAT}		39			dBm
Drain Efficiency @ P _{SAT}		35			%
Unless otherwise noted: TA = 25°C, V _{DD}	=28 V, Pulse Width=100 us, Duty cyc	le=10%			

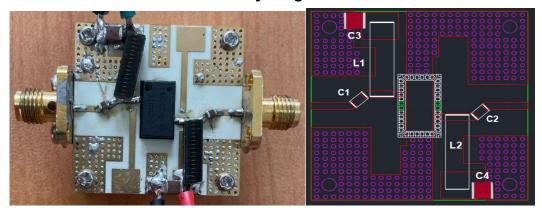
Load Mismatch of per Section (On Test Fixture, 50 ohm system): $V_{DD} = 28 \text{ V}$, $I_{DQ} = 40 \text{ mA}$, f = 1.6 GHz

VSWR 10:1 at Psat pulse CW Output Power	No Device Degradation
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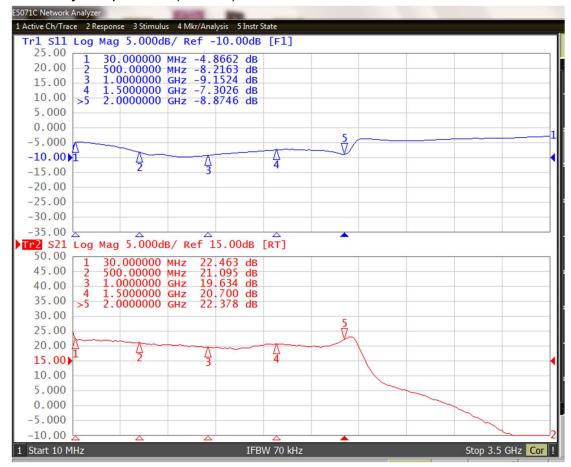
Reference Circuit of Test Fixture Assembly Diagram



		Part NO.	Vendor
C3,C4	10uF 100V chip Capacitor	C5750X7S2A106M230KB	TDK
C1,C2	50V 1uF Chip Capacitor	GRM21BR71H105KA12L	muRuta
L1,L2	1.3 uH 4.2A Inductor	4310LC-132KEC	Coilcraft
PCB	RO4350B,20mil,er=3.48		

TYPICAL CHARACTERISTICS

Figure 1. Network analyzer output S11/S21 (Pin=0dBm)

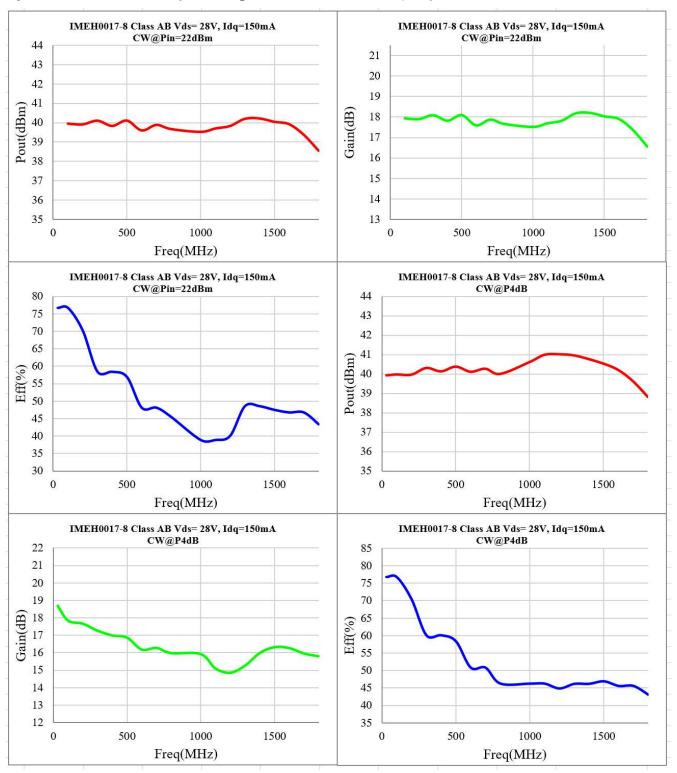




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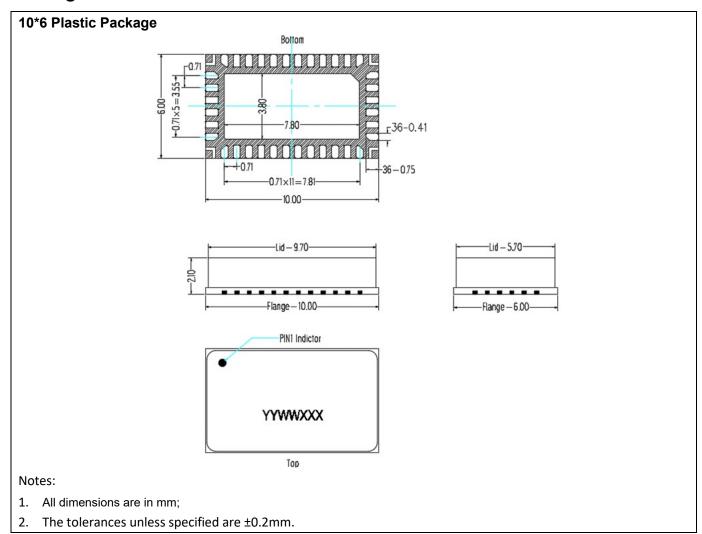
Figure. Power Gain and, efficiency and Pout @Pin=22dBm ,and P4dB vs. Frequency



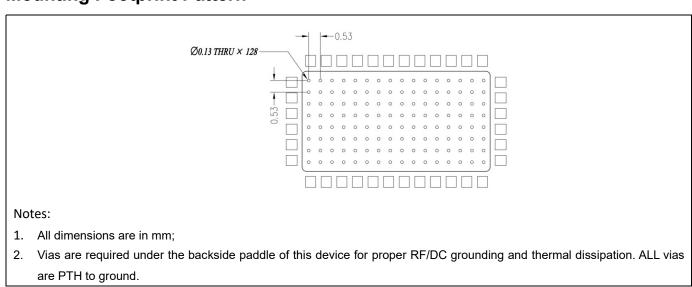
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Package Dimensions



Mounting Footprint Pattern



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Revision history

Table 6. Document revision history

Date	Revision	Datasheet Status
2022/12/9	Rev 1.0	Production Datasheet

Application data based on ZHH-22-02

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